

Super Barrier Rectifier™

Using state-of-the-art SBR IC process technology,
the following features are made possible in a single device:

Major ratings and characteristics

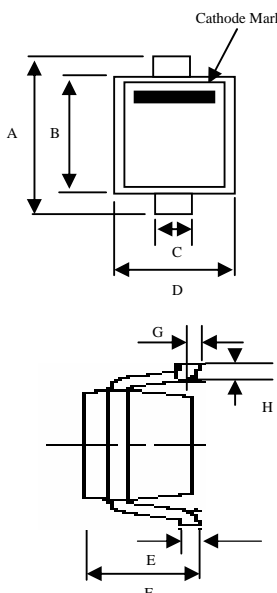
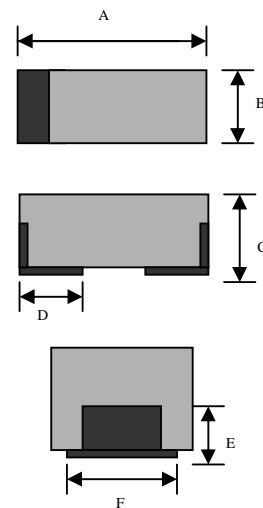
Characteristics	Values	Units
$I_{F(AV)}$ Rectangular Waveform	0.2	A
V_{RRM}	40	V
$V_F @ 0.2A, T_J = 75^\circ C$	0.54	V, typ
T_J (operating/storage)	-65 to 125	$^\circ C$

ELECTRICAL:

- * Low Forward Voltage Drop
- * Low Reverse Leakage
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * $125^\circ C$ Operating Junction Temperature

MECHANICAL:

- * Molded Plastic SOD-323, SOD-523 packages

SBR0240S3	SBR0240S5																																																						
<div><p>Cathode Mark</p></div> <div><table><tr><th colspan="3">SOD-323</th></tr><tr><th>Di</th><th>Min</th><th>Max</th></tr><tr><td>A</td><td>2.30</td><td>2.70</td></tr><tr><td>B</td><td>1.60</td><td>1.80</td></tr><tr><td>C</td><td>0.25</td><td>0.40</td></tr><tr><td>D</td><td>1.15</td><td>1.45</td></tr><tr><td>E</td><td>0.10</td><td>0.18</td></tr><tr><td>F</td><td>0.85</td><td>1.05</td></tr><tr><td>G</td><td>-</td><td>0.10</td></tr><tr><td>H</td><td>0.20</td><td>0.40</td></tr></table><p>All Dimensions in mm</p></div> <div>SOD-323</div>	SOD-323			Di	Min	Max	A	2.30	2.70	B	1.60	1.80	C	0.25	0.40	D	1.15	1.45	E	0.10	0.18	F	0.85	1.05	G	-	0.10	H	0.20	0.40	<div></div> <div><table><tr><th colspan="3">SOD-523</th></tr><tr><th>Di</th><th>Min</th><th>Max</th></tr><tr><td>A</td><td>1.60</td><td>1.80</td></tr><tr><td>B</td><td>0.8</td><td>1.0</td></tr><tr><td>C</td><td>0.70</td><td>0.85</td></tr><tr><td>D</td><td colspan="2">0.35 (typ)</td></tr><tr><td>E</td><td colspan="2">0.30 (typ)</td></tr><tr><td>F</td><td colspan="2">0.70 (typ)</td></tr></table><p>All Dimensions in mm</p></div> <div>SOD-523</div>	SOD-523			Di	Min	Max	A	1.60	1.80	B	0.8	1.0	C	0.70	0.85	D	0.35 (typ)		E	0.30 (typ)		F	0.70 (typ)	
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Maximum Ratings and Electrical Characteristics (at 25°C unless otherwise specified)				
	SYMBOL			UNITS
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V_{RM} V_{RWM} V_{RRM}	40		Volts
Average Rectified Forward Current (Rated V_R - 20Khz Square Wave) - 50% duty cycle	I_O	0.2		Amps
Peak Forward Surge Current - 1/2 60hz	I_{FSM}	2		Amps
Instantaneous Forward Voltage $I_F = 200mA$; $T_J = 25^\circ C$ $I_F = 200mA$; $T_J = 75^\circ C$	V_F	Typ --- ---	Max 0.60 0.58	Volts
Maximum Reverse Current at Rated V_{RM} $T_J = 25^\circ C$ $T_J = 75^\circ C$	I_R^*	Typ --- ---	Max 15 200	μA μA
Operating and Storage Junction Temperature	T_J	-65 to +125		$^\circ C$

NOTE: Dice are available for customer applications.

* Pulse width < 300 μs , Duty cycle < 2%

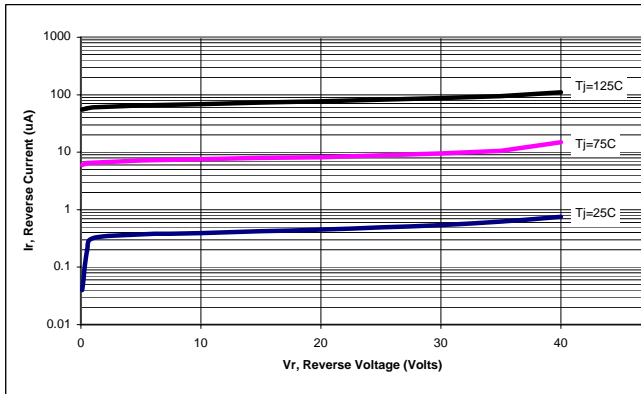


Figure 1: Typical Reverse Current

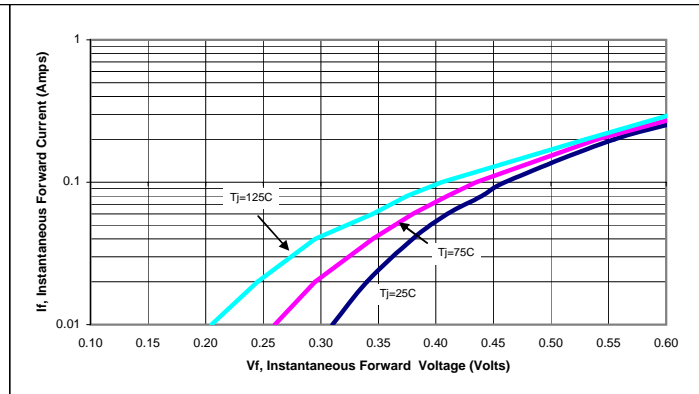


Figure 2: Typical Forward Voltage

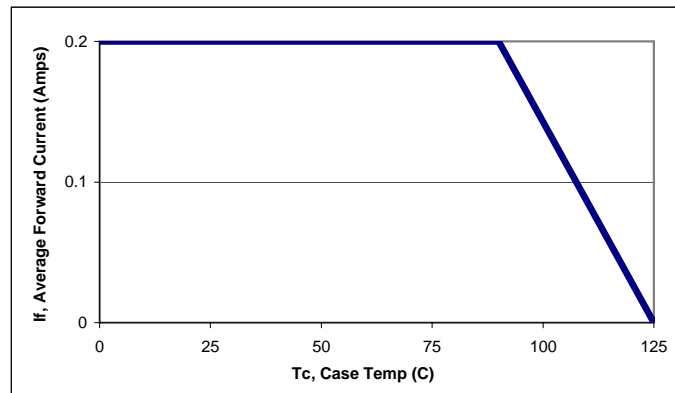


Figure 3: Current Derating, Case

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